

SPTECH Silicon NPN Power Transistor

BU406D

DESCRIPTION

- High Voltage: $V_{CEV} = 300V(\text{Min})$
- Low Saturation Voltage-
: $V_{CE(sat)} = 1.0V(\text{Max.}) @ I_C = 5A$

APPLICATIONS

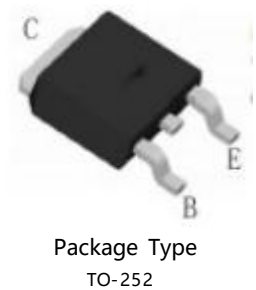
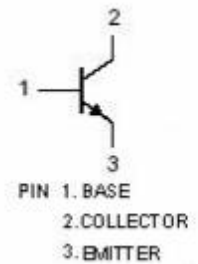
- Designed for use in horizontal deflection output stages of TV's and CRT's

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector- Base Voltage	300	V
V_{CEO}	Collector- Emitter Voltage	150	V
V_{EBO}	Emitter- Base Voltage	6	V
I_C	Collector Current- Continuous	7	A
I_{CP}	Collector Current- Peak Repetitive	10	A
I_{CP}	Collector Current- Peak (10ms)	15	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	65	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.08	$^\circ C / W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	70	$^\circ C / W$



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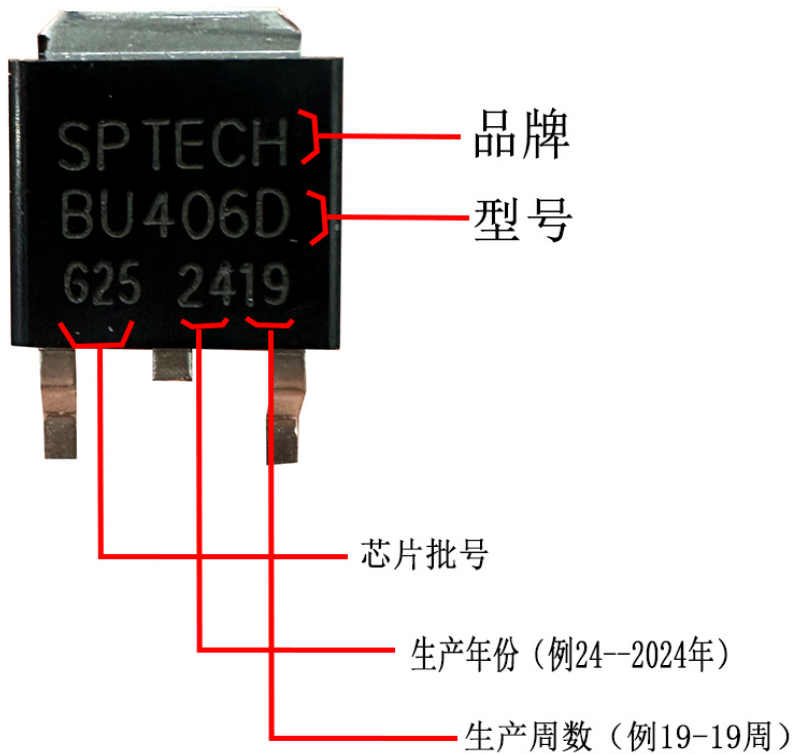
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ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

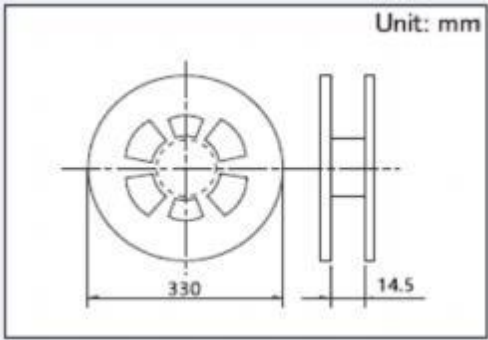
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector- Emitter Sustaining Voltage	$I_C = 50\text{mA}; I_B = 0$	150			V
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 0.8\text{A}$			1.0	V
$V_{BE(sat)}$	Base- Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 0.5\text{A}$			1.2	V
I_{CES}	Collector Cutoff Current	$V_{CE} = 300\text{V}; V_{BE} = 0$ $V_{CE} = 150\text{V}; V_{BE} = 0$			5.0 0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 6\text{V}; I_C = 0$			1.0	mA
h_{FE}	DC Current Gain	$I_C = 2\text{A}; V_{CE} = 5\text{V}$	60	70	80	
f_T	Current-Gain— Bandwidth Product	$I_C = 0.5\text{A}; V_{CE} = 10\text{V}$	10	30		MHz
t_f	Fall Time	$I_C = 5\text{A}; I_{B1} = -I_{B2} = 0.8\text{A}$			0.4	μs

丝印工艺说明



包装规格

载带:



包装数量 (PCS):

一卷	2500
一盒	5000
一箱	20000

包装尺寸 (mm):

盒装	338*338*35
箱装	360*360*45

BU406D TO-252尺寸图

